





SWITCHING REGULATOR APPLICATIONS

Features

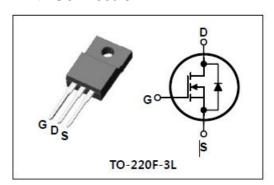
•High Voltage: BV_{DSS}=650V(Min.)

•Low C_{rss} : $C_{rss}=5.6pf(Typ.)$

•Low: gate charge: Qg=11.2nC(Typ.)

•Low $R_{DS(on)}$: $R_{DS(on)}$ =3.0 Ω (Max.)

PIN Connection



Ordering Information

| Type NO. | Marking | Package Code |
|--------------|----------|--------------|
| KMK0465F | KMK0465• | TO-220F-3L |
| KMK0465F(HF) | KMK0465• | TO-220F-3L |

*KMK0465F: Pd Free Product

*KMK0465F(HF): Halogen Free product

Marking Diagram



Column 1 : Manufacturer

Column 2: Production Information

e.g.) GFYMDD

-. G : Option Code (H : Halogen Free) -. F : Factory Management Code -. YMDD : Date Code (Year, Month, Date)

Column 3 : Device Code

Absolute maximum ratings (Tc=25°C unless otherwise noted)

| Characteristic | Symbol | | Ratings | Unit |
|----------------------------------|-------------------------|------------------|----------------------|------|
| Drain-source voltage | | Vdss | 650 | V |
| Gate-source voltage | | Vgss | ±30 | V |
| Decision and (DC) th | т | Tc=25° C | 4 | A |
| Drain current(DC)* | ID | Tc=100° C | 2. 0 | A |
| Drain current(pulsed) * | n current(pulsed) * IDM | | 16 | A |
| Power dissipation | PD | | 30 | W |
| Avalanche current(single) ② | | Ias | 4 | A |
| Single pulsed avalanche energy ② | | Eas | 81.5 | mJ |
| Avalanche current(Repetitive) ① | | Iar | 4 | A |
| Repetitive avalanche energy ① | | Ear | 3. 4 | mJ |
| Junction temperature | | Тл | 150 | °C |
| Storage temperature range | $T_{ m stg}$ | | -55 [~] 150 | |

^{* :} Limited by maximum junction temperature

| Characte | ristic | Symbol | Тур. | Max | Unit |
|------------|------------------|-----------|------|------|---------|
| Thermal | Junction-case | Rth (J-C) | - | 4.16 | °C /\\\ |
| resistance | Junction-ambient | Rth (J-A) | - | 62.5 | °C/W |

Electrical Characteristics (Tc=25°C unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|----------------------------------|---------------------|--|------|------|------|------|
| Drain-source breakdown voltage | BV _{DSS} | In=250uA, Vgs=0 | 650 | - | - | V |
| Gate threshold voltage | V _{GS(th)} | In=250uA, Vns=Vgs | 2.0 | - | 4.0 | V |
| Drain-source cut-off current | Idss | V _{DS} =650V, V _{GS} =0V | - | - | 1 | μΑ |
| Gate leakage current | Igss | $V_{DS}=0V$, $V_{GS}=\pm30V$ | - | - | ±100 | nA |
| Drain-source on-resistance 4 | Rds(on) | V _G S=10V I _D =2.0A | - | 2.4 | 3.0 | Ω |
| Forward transfer conductance (4) | G fs | V _{DS} =10V I _D =2.0A | - | 4.0 | - | S |
| Input capacitance | Ciss | V 40V V 25V | - | 703 | 878 | |
| Ourput capacitance | Coss | VGS=10V, V DS=25V F=1MHz | - | 54.6 | 68.2 | pF |
| Reverse transfer capacitance | Crss | 1 – 111112 | - | 5.6 | 7.0 | |
| Turn-on delay time | t d(on) | | - | 10 | - | |
| Rise time | tr | $V_{DD} = 300V$, $I_{D} = 4.0A$ $R_{G} = 25 \Omega$ 34 | - | 42 | - | |
| Turn-off delay time | Td(off) | | - | 38 | - | ns |
| Fall time | t f | | - | 46 | - | |
| Total gate charge | Qg | V 520V V 40V | - | 11.2 | 14.0 | |
| Gate-source charge | Qgs | V _{DS} =520V, V _{GS} =10V I _D =4.0A 34 | - | 3.9 | - | nC |
| Gate-drain charge | Qgd | | - | 2.5 | - | |

$\textbf{Source-Drain Diode Ratings and Characteristics} (Tc = 25^{\circ}C \ unless \ otherwise \ noted)$

| Characteristic | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|--------------------------|--------|----------------------------------|-----|------|-----|------|--|
| Source current(DC) | Is | Integral revere diode | - | - | 4 | Λ | |
| Source current(pulsed) ① | Ism | In the MOSFET | - | - | 16 | Α | |
| Forward voltage ④ | Vsd | Vgs=0V, Is=4.0A | - | - | 1.4 | V | |
| Reverse recovery time | trr | Is=4.0A,VGS=0V dIf/dt=100A/us | - | 300 | - | ns | |
| Reverse recovery charge | Qrr | | 1 | 2.2 | - | uС | |

Note:

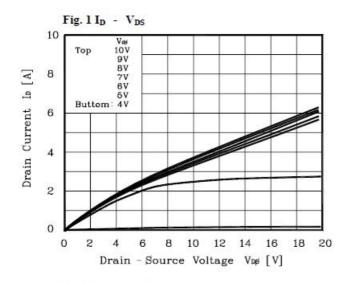
 ${\color{black} \textcircled{1}}$ Repetitive rating : Pulse width limited by maximum junction temperature

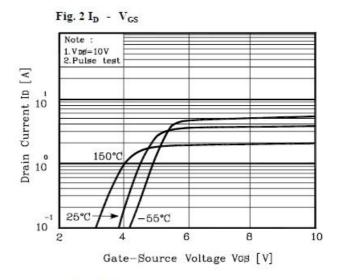
 $\ \, \mbox{(2)} \ \mbox{L=9.4mH, IAS=4.0A, VDD=50V, RG=25}\,\Omega\,\mbox{, Starting TJ=25}\,^{\circ}\ \mbox{C}$

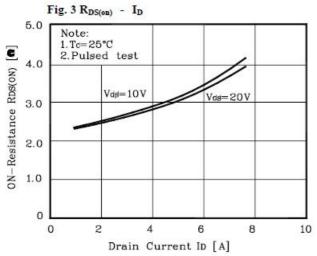
③ Pulse Test: Pulse width≤300us, Duty cycle≤2%

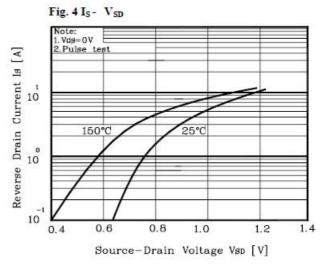
4 Essentially independent of operating temperature

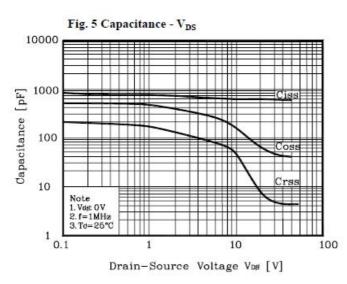
Electrical Characteristic Curves

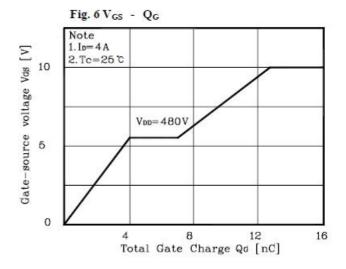




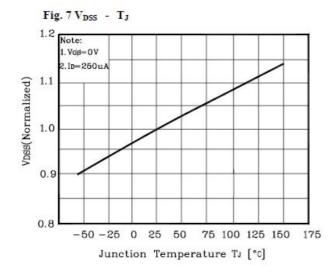


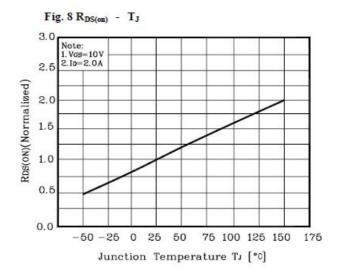


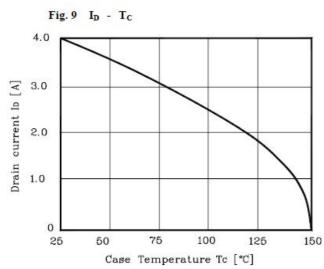




Electrical Characteristic Curves







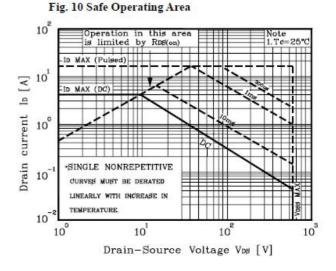


Fig. 11 Gate Charge Test Circuit & Waveform

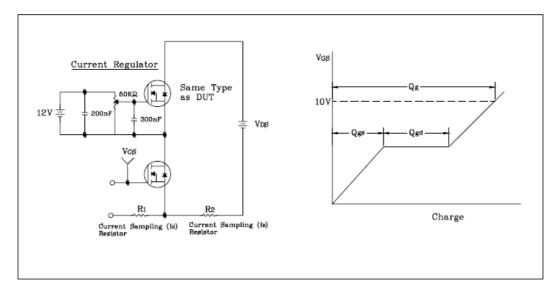


Fig. 12 Resistive Switching Test Circuit & Waveform

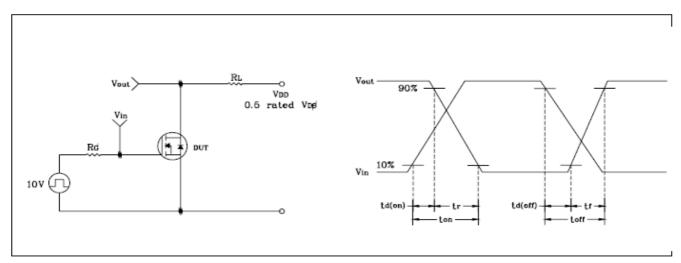


Fig. 13 Eas Test Circuit & Waveform

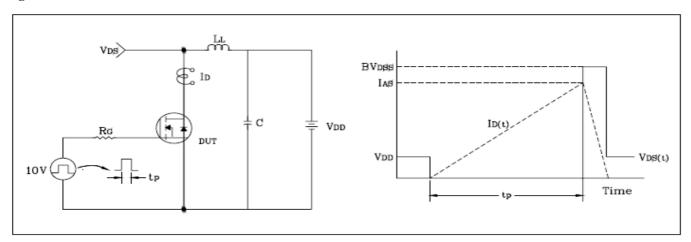
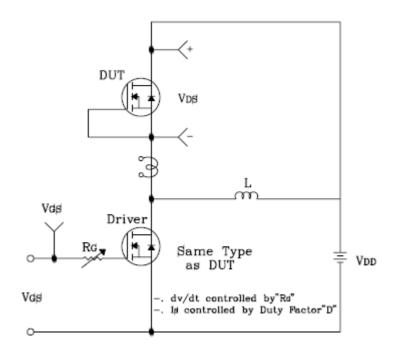
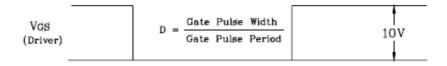
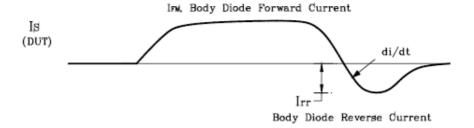
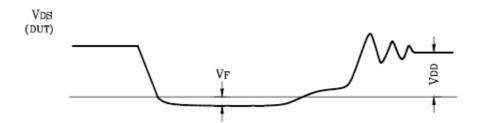


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



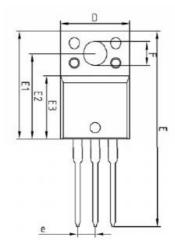


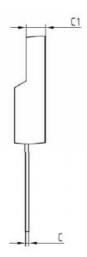


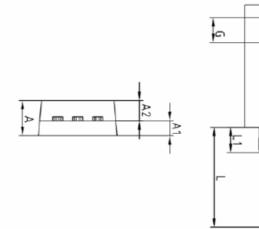


Outline Dimension









| | | NOTE | | |
|--------|---------|---------|---------|------|
| SYMBOL | MINIMUM | NOMINAL | MAXIMUM | NOIL |
| A | - | - | 4.60 | |
| A1 | 2.45 | 2.50 | 2.55 | |
| A2 | 1.95 | 2.00 | 2.05 | |
| ь | 0.65 | 0.75 | 0.85 | |
| ь1 | 1.07 | 1.27 | 1.47 | |
| С | 0.40 | 0.50 | 0.60 | |
| C1 | 2.70 | 2.80 | 2.90 | |
| D | 9.90 | 10.00 | 10.10 | |
| Ε | 28.00 | - | 28.60 | |
| E1 | 15.50 | 15.60 | 15.70 | |
| E2 | 12.30 | 12.40 | 12.50 | |
| E3 | 9.15 | 9.20 | 9.25 | |
| F | 3,30 | 3.40 | 3.50 | |
| G | 3.10 | 3.20 | 3.30 | |
| e | | | | |
| L | 12.40 | 3.46 BS | 13.00 | |
| L1 | | | | |

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